

L Number	Hits	Search Text	DB	Time stamp
11	2342	438/257	USPAT	2004/09/23 17:53
12	873	438/259	USPAT	2004/09/23 17:53
13	573	438/263	USPAT	2004/09/23 17:53
14	1373	438/264	USPAT	2004/09/23 17:53
15	781	438/266	USPAT	2004/09/23 17:53
16	520	438/267	USPAT	2004/09/23 17:53
17	432	438/265	USPAT	2004/09/23 17:53
18	522	438/276	USPAT	2004/09/23 17:53
19	360	438/278	USPAT	2004/09/23 17:53
20	499	438/294	USPAT	2004/09/23 17:54
21	1047	438/299	USPAT	2004/09/23 17:54
22	899	438/286	USPAT	2004/09/23 17:54
-	1	10/143225	USPAT	2004/09/23 16:27
-	1	10/143225 and (EEPROM or CMP or nonvolatile or memory or cell or nitride or ONO or silicon or oxide or floating or gate or control or poly or polysilicon or transistor or pair or pairs or remnants or material or oppsite or lateral or member or spaced or spacer or insulator or insulated or independent or two or substrate or side or insulative or protective or electrically or highly or doped or region or bit or word or line or ion or implantation or implanting or phased or lines)	USPAT	2004/09/23 16:43
-	1		USPAT	2004/09/23 16:40
-	1	"6369422".PN. and (EEPROM or CMP or nonvolatile or memory or cell or nitride or ONO or silicon or oxide or floating or gate or control or poly or polysilicon or transistor or pair or pairs or remnants or material or oppsite or lateral or member or spaced or spacer or insulator or insulated or independent or two or substrate or side or insulative or protective or electrically or highly or doped or region or bit or word or line or ion or implantation or implanting or phased or lines)	USPAT	2004/09/23 16:54
-	3	09/847810	USPAT	2004/09/23 16:45
-	1	("6486031").PN.	USPAT	2004/09/23 16:45
-	1	((("6486031").PN.) and (EEPROM or CMP or nonvolatile or memory or cell or nitride or ONO or silicon or oxide or floating or gate or control or poly or polysilicon or transistor or pair or pairs or remnants or material or oppsite or lateral or member or spaced or spacer or insulator or insulated or independent or two or substrate or side or insulative or protective or electrically or highly or doped or region or bit or word or line or ion or implantation or implanting or phased or lines)	USPAT	2004/09/23 16:55
-	1		USPAT	2004/09/23 16:51
-	1		USPAT	2004/09/23 16:51
-	1		USPAT	2004/09/23 16:51
-	1		USPAT	2004/09/23 16:51
-	1		USPAT	2004/09/23 16:51
-	1		USPAT	2004/09/23 16:51
-	1		USPAT	2004/09/23 16:53
-	1		USPAT	2004/09/23 16:54
-	1		USPAT	2004/09/23 16:54
-	0	(two adj poly adj remnants) and (highly adj doped adj regions) and (floating adj poly adj member)	USPAT	2004/09/23 16:57
-	0	(two adj poly adj remnants) and (highly adj doped) and (floating adj poly adj member)	USPAT	2004/09/23 17:03
-	0	(poly adj remnants) and (highly adj doped) and (floating adj poly adj member)	USPAT	2004/09/23 16:58
-	0	(two adj independent adj memory adj transistors) and floating and control and gate and polysilicon and highly and doped	USPAT	2004/09/23 17:01
-	0	(two adj independent adj memory adj transistors)	USPAT	2004/09/23 17:01

-	0	(independent adj memory adj transistors) and floating and control and gate and polysilicon and highly and doped	USPAT	2004/09/23 17:01
-	0	(two adj poly adj remnants) and (floating adj poly adj member)	USPAT	2004/09/23 17:03
-	0	self-aligned adj highly adj doped adj regions	USPAT	2004/09/23 17:04
-	6	self-aligned adj highly adj doped	USPAT	2004/09/23 17:04
-	6	(self-aligned adj highly adj doped) and (EEPROM or nonvolatile or memory or cell or transistor or polysilicon or control or gate or floating or ion or implantation or implanting or oxide or nitride or two or pairs or remnants or member or poly or CMP or lateral or sides or opposite or independent)	USPAT	2004/09/23 17:52

9/23/04